

10/023113

12/13/01

PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10023113	FILING DATE 12/13/2001	CLASS 265	SUBCLASS	GAU 2818	EXAMINER
<b>**APPLICANTS:</b> Marshall Andrew Kim Youngmin Scott David Mercer Douglas					
<b>**CONTINUING DATA VERIFIED:</b> THIS APPLN CLAIMS BENEFIT OF 60/159 324 01 03 2001					
<h1>BEST AVAILABLE COPY</h1>					
<b>** FOREIGN APPLICATIONS VERIFIED:</b>					
PG-PUB <input type="checkbox"/> DO NOT PUBLISH <input type="checkbox"/>		RESCIND <input type="checkbox"/>			
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO	
Verified and Acknowledged Examiners' initials				TI-31157	
<b>TITLE :</b> Memory cell with transistors having relatively high threshold voltages in response to selective gate doping					

<b>NOTICE OF ALLOWANCE MAILED</b>		<b>CLAIMS ALLOWED</b>	
		Total Claims	Print Claim for O.G.
<b>ISSUE FEE</b>		<b>DRAWING</b>	
Amount Due	Date Paid	Sheets Drwg.	Figs.Drwg. Print Fig.
<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>		Primary Examiner	
		Application Examiner	
<b>PREPARED FOR ISSUE</b>		<b>WARNING:</b> The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.	

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